Silicon NPN Power Transistors 2SD1402

DESCRIPTION

- With TO-3PN package
- High speed switching
- High voltage,high reliability
- Wide area of safe operation

APPLICATIONS

- For CRT horizontal output applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter



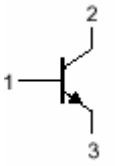


Fig.1 simplified outline (TO-3PN) and symbol

Absolute maximum ratings (Ta=25℃)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	1500	V
V_{CEO}	Collector-emitter voltage	Open base	800	V
V_{EBO}	Emitter-base voltage	Open collector	6	V
I_C	Collector current		5	A
P_C	Collector power dissipation	T_C=25℃	120	W
T_j	Junction temperature		150	℃
T_{stg}	Storage temperature		-55~150	℃

Silicon NPN Power Transistors 2SD1402

CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-emitter sustaining voltage	I_C=100mA; I_B=0	800			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	I_E=1mA; I_C=0	6			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=4A; I_B=0.8A			5.0	V
V_{BEsat}	Base-emitter saturation voltage	I_C=4A; I_B=0.8A			1.5	V
I_{CBO}	Collector cut-off current	V_{CB}=800V; I_E=0			10	μA
I_{EBO}	Emitter cut-off current	V_{EB}=4V; I_C=0			10	μA
h_{FE}	DC current gain	I_C=1A ; V_{CE}=5V	8			
f_T	Transition frequency	I_C=1A ; V_{CE}=10V		3		MHz

Silicon NPN Power Transistors 2SD1402

PACKAGE OUTLINE

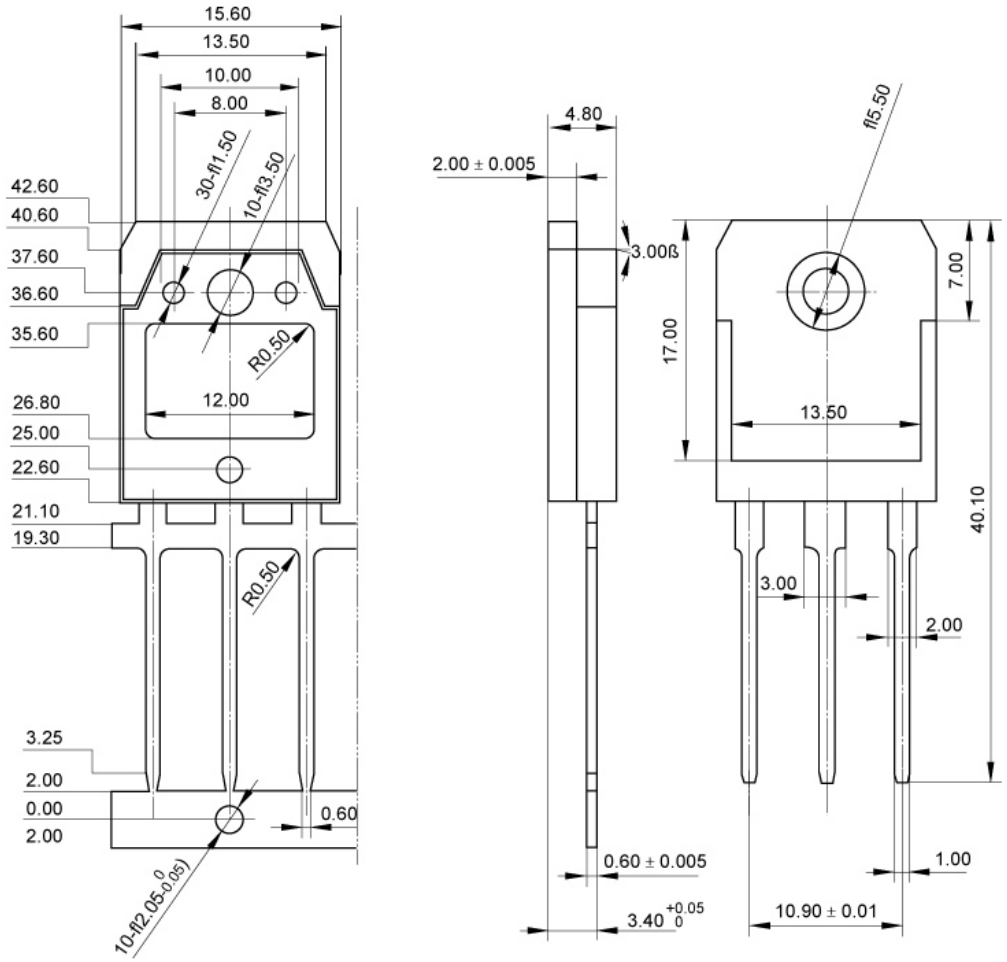


Fig.2 outline dimensions (unindicated tolerance:±0.10 mm)